



# STL100N1VH5

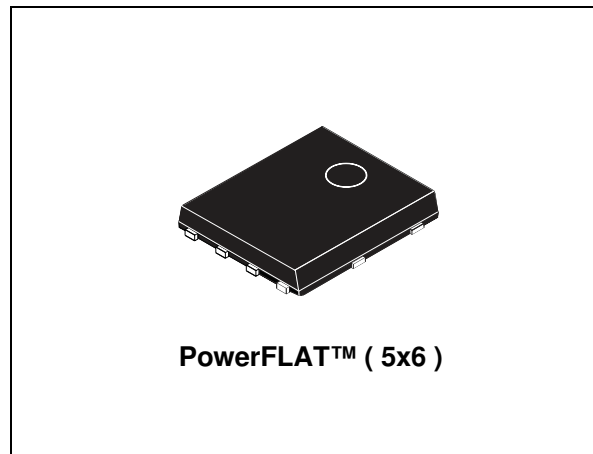
N-channel 12 V, 0.0022  $\Omega$ , 25 A PowerFLAT™ (5x6)  
STripFET™ V Power MOSFET

## Features

Order code	V <sub>DSS</sub>	R <sub>DS(on) max.</sub>	I <sub>D</sub>
STL100N1VH5	12 V	<0.003 $\Omega$	25 A <sup>(1)</sup>

1. The value is rated according R<sub>thj-pcb</sub>

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses



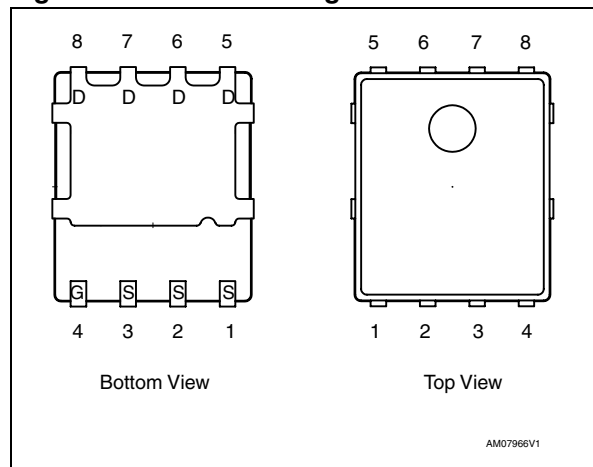
## Application

Switching applications

## Description

This device is a 12 V N-channel STripFET™ V Power MOSFET which has been designed to achieve very low on-state resistance providing also one of the best-in-class figure of merit (FOM).

**Figure 1. Pin-out configuration**



**Table 1. Device summary**

Order code	Marking	Package	Packaging
STL100N1VH5	100N1VH5	PowerFLAT™ (5x6)	Tape and reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>8</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>9</b>
<b>5</b>	<b>Revision history</b> .....	<b>12</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	12	V
$V_{GS}$	Gate-source voltage	$\pm 8$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	100	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	62.5	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	25	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	15.6	A
$I_{DM}^{(3)}$	Drain current (pulsed)	100	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25^\circ\text{C}$	60	W
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
$T_J$	Operating junction temperature	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		

1. The value is rated according  $R_{thj-c}$
2. The value is rated according  $R_{thj-pcb}$
3. Pulse width limited by safe operating area

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (Drain) (steady state)	2.08	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	31.3	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10$  sec

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AV}$	Not-repetitive avalanche current (pulse width limited by $T_J$ Max)	12.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25^\circ\text{C}$ , $I_D = I_{AV}$ , $V_{DD} = 12$ V)	300	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	12			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max rating}$ , $V_{DS} = \text{max rating @ } 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	0.5			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 4.5\text{ V}$ , $I_D = 12.5\text{ A}$ $V_{GS} = 2.5\text{ V}$ , $I_D = 12.5\text{ A}$		0.0022 0.0032	0.003 0.004	$\Omega$ $\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ISS}$	Input capacitance	$V_{DS} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	2085	-	pF
$C_{OSS}$	Output capacitance			949		pF
$C_{RSS}$	Reverse transfer capacitance			240		pF
$Q_g$	Total gate charge	$V_{DD} = 6\text{ V}$ , $I_D = 12.5\text{ A}$	-	26.5	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 4.5\text{ V}$		5.2		nC
$Q_{gd}$	Gate-drain charge	<a href="#">Figure 14</a>		4.8		nC

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=6\text{ V}$ , $I_D=12.5\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=4.5\text{ V}$ <i>Figure 13</i>	-	14.4	-	ns
$t_r$	Rise time			31.6		ns
$t_{d(off)}$	Turn-off delay time			50		ns
$t_f$	Fall time			16		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		25	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		100	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=25\text{ A}$ , $V_{GS}=0$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD}=25\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$ , $V_{DD}=10\text{ V}$ , $T_j=150\text{ }^\circ\text{C}$	-	49		ns
$Q_{rr}$	Reverse recovery charge			54		nC
$I_{RRM}$	Reverse recovery current			2.2		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration= 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

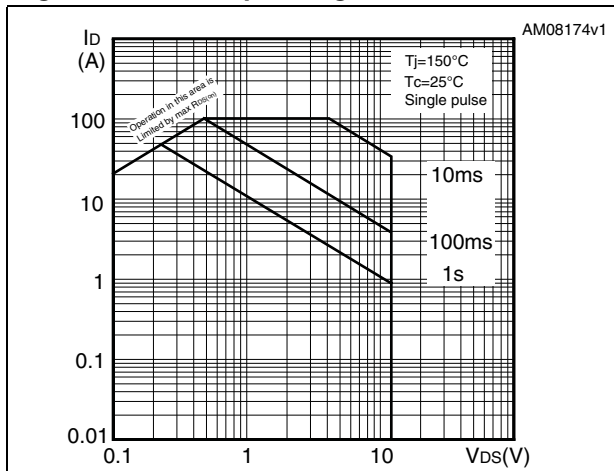


Figure 3. Thermal impedance

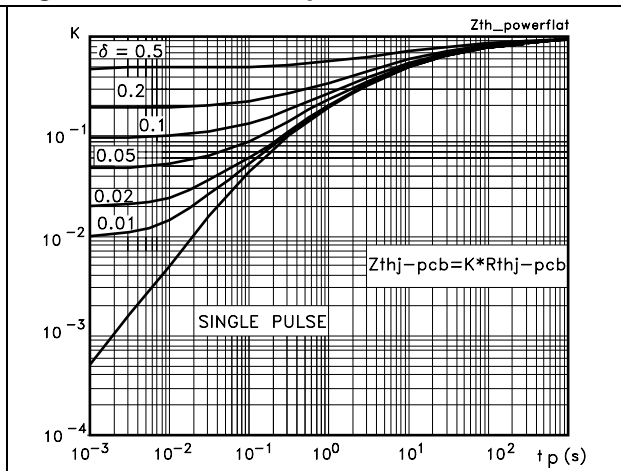


Figure 4. Output characteristics

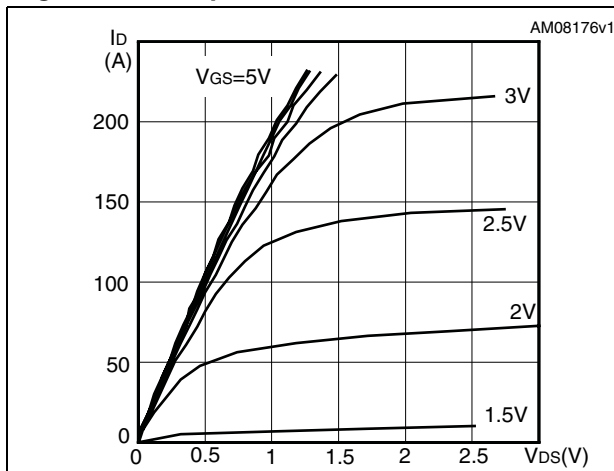


Figure 5. Transfer characteristics

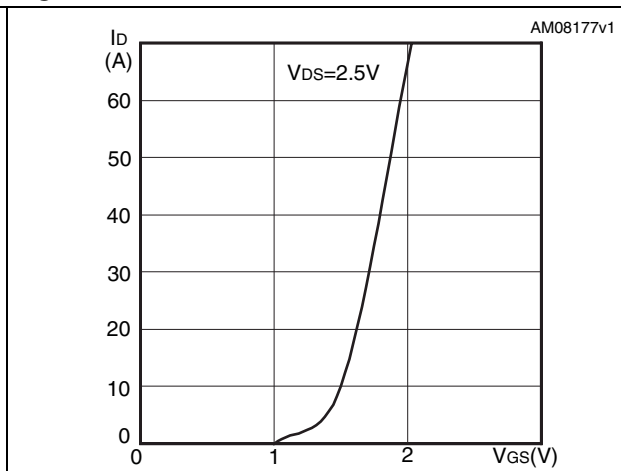


Figure 6. Normalized  $B_{VDSS}$  vs temperature

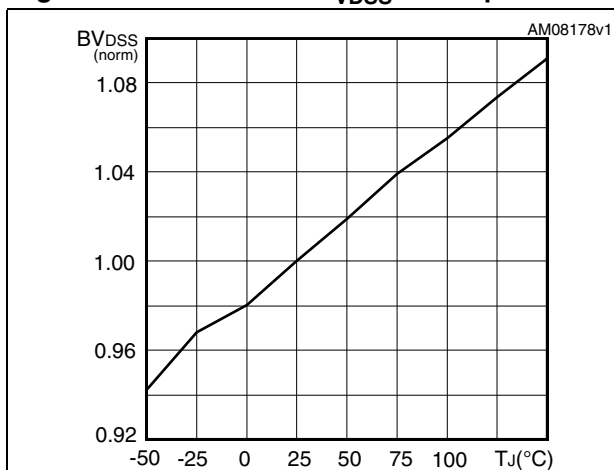


Figure 7. Static drain-source on resistance

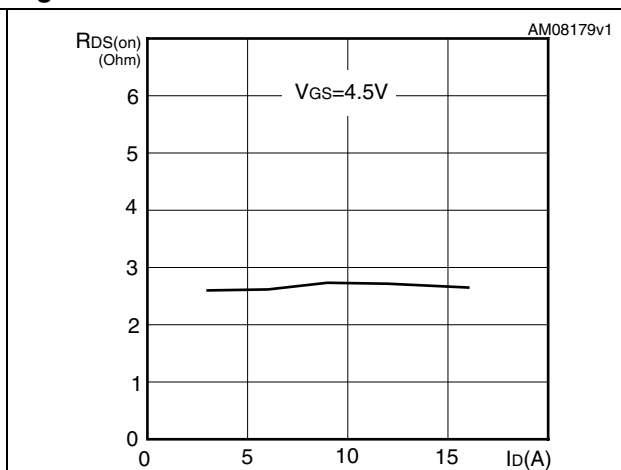


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

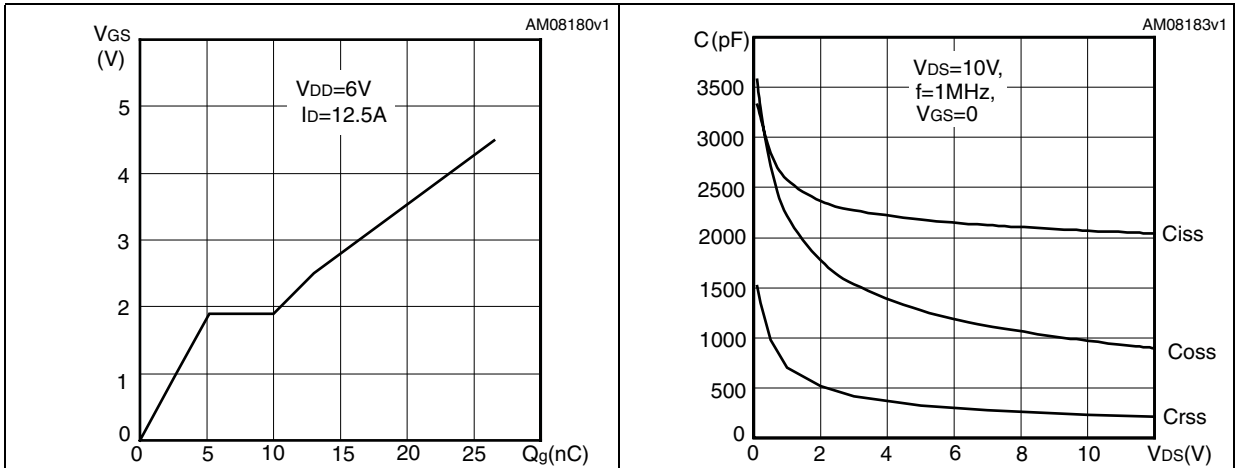


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

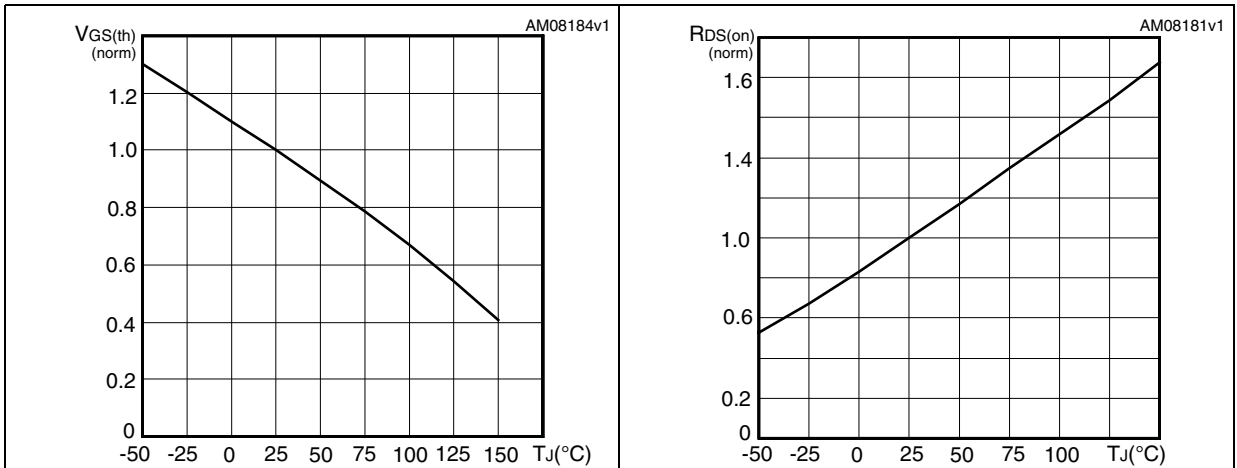
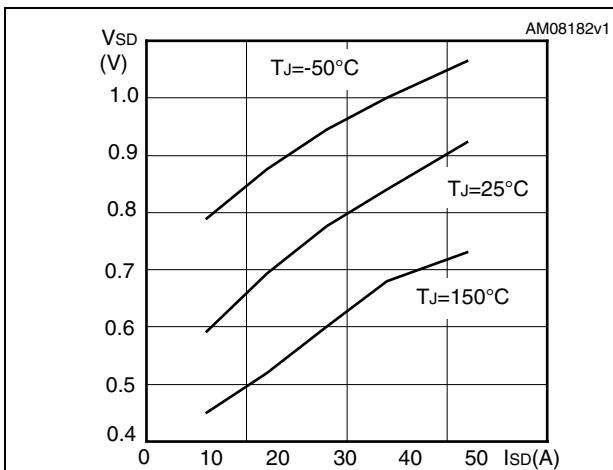
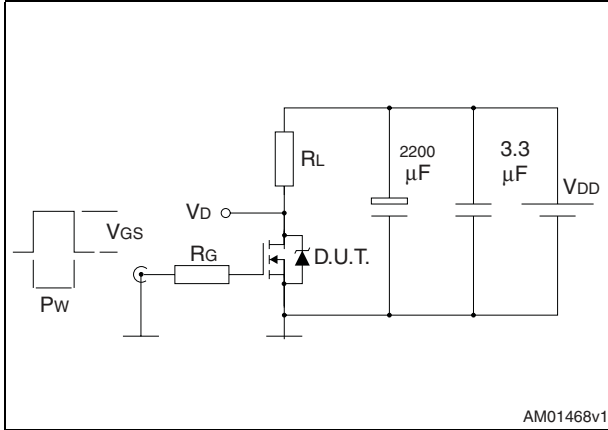


Figure 12. Source-drain diode forward characteristics

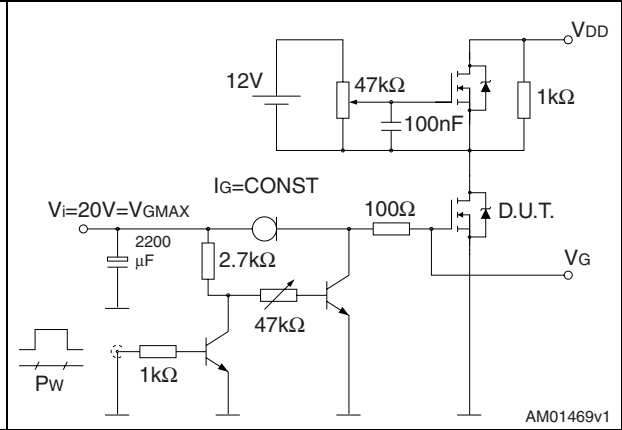


### 3 Test circuits

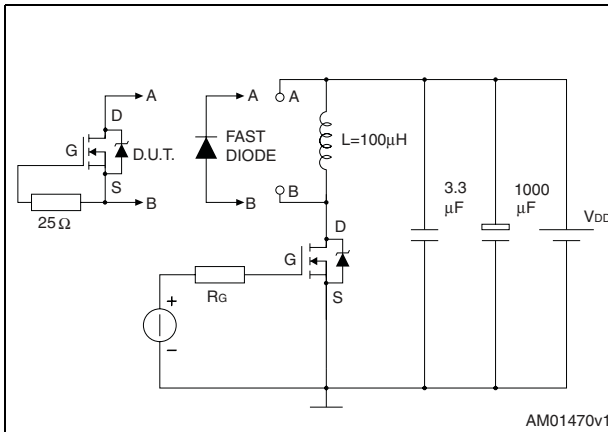
**Figure 13. Switching times test circuit for resistive load**



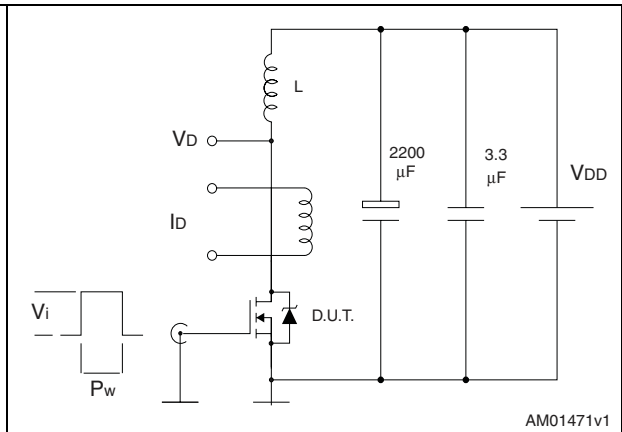
**Figure 14. Gate charge test circuit**



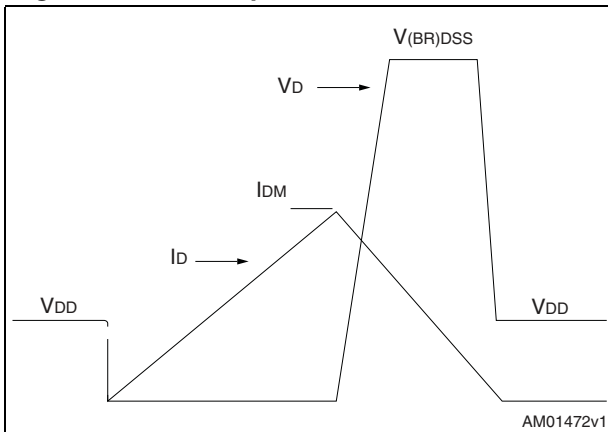
**Figure 15. Test circuit for inductive load switching and diode recovery times**



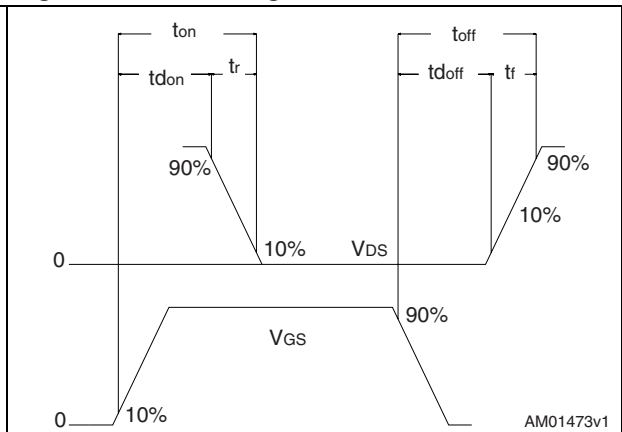
**Figure 16. Unclamped inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**





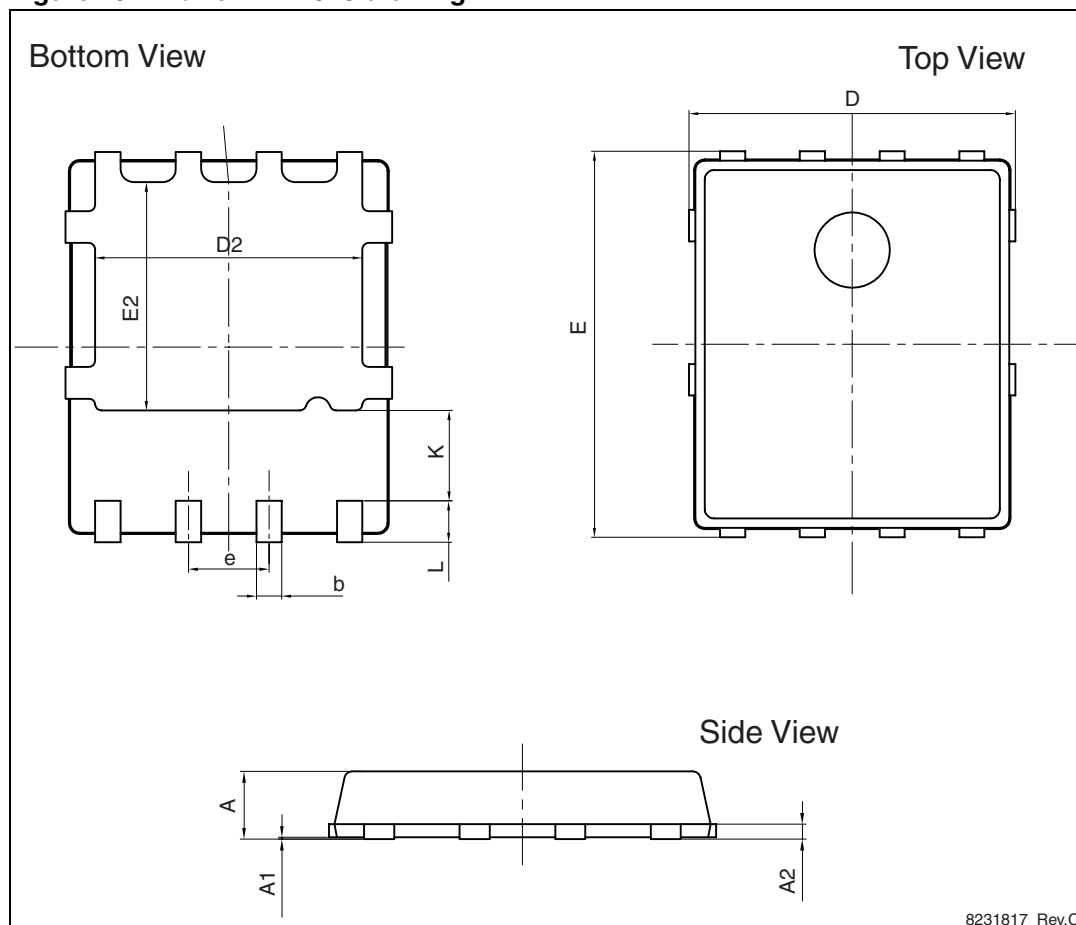
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 9. PowerFLAT 5x6 mechanical data

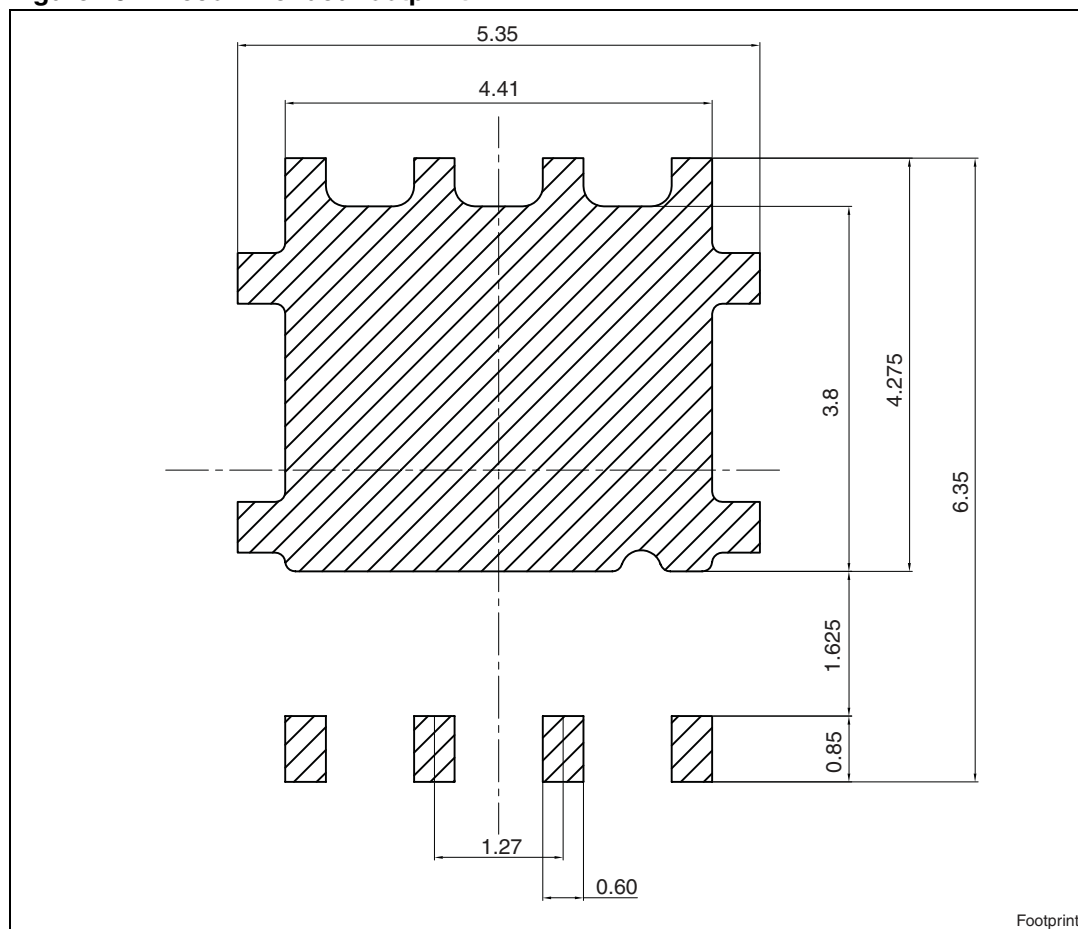
Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Figure 19. PowerFLAT 5x6 drawing



8231817\_Rev.C

Figure 20. Recommended footprint



## 5 Revision history

Table 10. Document revision history

Date	Revision	Changes
10-Mar-2011	1	First release.

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)

